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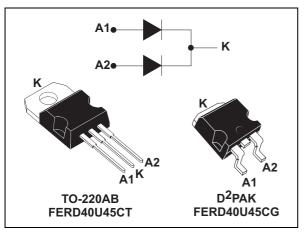




FERD40U45C

Field effect rectifier

Datasheet - production data



Features

- ST advanced rectifier process
- Stable leakage current over reverse voltage
- Low forward voltage drop
- High frequency operation

Description

This dual rectifier is based on a proprietary technology that achieves the best in class $V_{\rm F}/I_{\rm R}$ for a given silicon surface.

Packaged in TO-220AB, and D^2PAK , this device is intended to be used in switch mode power supplies, or automotive applications

Table 1. Device summary

I _{F(AV)}	2 x 20 A
V _{RRM}	45 V
V _F (typ)	0.31 V

This is information on a product in full production.

1 Characteristics

Table 2. Absolute ratings (limiting values, per diode at 25° C, unless otherwise stated)

Symbol	Para	Value	Unit		
V _{RRM}	Repetitive peak reverse voltage			45	V
I _{F(RMS)}	Forward rms current			40	А
I _{F(AV)}	Average forward current, $\delta = 0.5$	T _c =150° C T _c =145° C	Per diode Per device	20 40	A
I _{FSM}	Surge non repetitive forward current	275	Α		
T _{stg}	Storage temperature range	-65 to + 175	°C		
	Maximum operating junction	TO-220AB, D ² PA	TO-220AB, D ² PAK		
Тj	temperature ⁽¹⁾		D^2PAK (DC forward current without reverse bias, t = 1 hour)		°C

1. $\frac{dPtot}{dTj} < \frac{1}{Rth(j-a)}$ condition to avoid thermal runaway for a diode on its own heatsink

Table 3. Thermal resistances

Symbol	Parameter	Parameter		
R _{th (j-c)}	Junction to case	Per diode Total	1.6 1.1	°C/W
R _{th(c)}	Coupling		0.5	°C/W

When the diodes 1 and 2 are used simultaneously:

 $\Delta T_{i}(\text{diode 1}) = P(\text{diode1}) \times R_{th(i-c)}(\text{Per diode}) + P(\text{diode2}) \times R_{th(c)}.$

Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Unit
I_(1)	I _B ⁽¹⁾ Reverse leakage current	$T_j = 25^\circ C$	$V_{R} = V_{RRM}$			1800	μA
'R` ´		T _j = 125° C			50	100	mA
	V _F ⁽²⁾ Forward voltage drop	T _j = 25° C	I _F = 10 A		0.35	0.385	
V (2)		T _j = 125° C			0.31	0.34	V
VF`		T _j = 25° C	1 00 4		0.42	0.46	v
		T _j = 125° C	I _F = 20 A		0.42	0.46	

1. Pulse test: $t_p = 5 \text{ ms}, \delta < 2\%$

2. Pulse test: t_p = 380 µs, δ < 2%

To evaluate the conduction losses use the following equation:

$$P = 0.28 \times I_{F(AV)} + 0.009 \ I_{F}{}^{2}_{(RMS)}$$



Figure 1. Average forward power dissipation versus average forward current (per diode) $P_{F(AV)}(W)$ $\downarrow_{\delta=0,1}^{P_{F}(AV)} = 0.2$

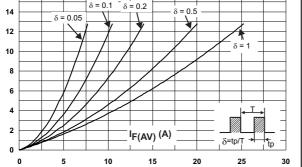


Figure 3. Relative variation of thermal impedance junction to case versus pulse duration

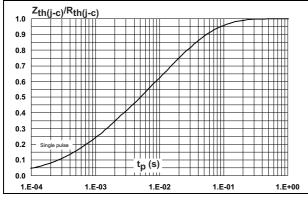


Figure 5. Junction capacitance versus reverse voltage applied (typical values, per diode)

Figure 2. Average forward current versus ambient temperature (δ = 0.5, per diode)

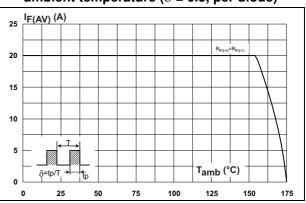


Figure 4. Reverse leakage current versus reverse voltage applied (typical values, per diode)

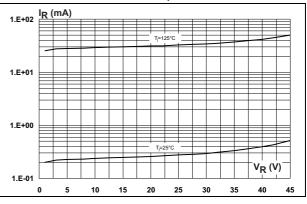
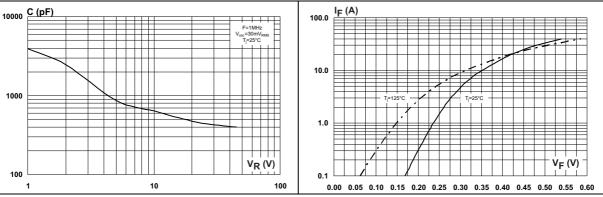


Figure 6. Forward voltage drop versus forward current (typical values, per diode)





80 Rt	h(j-a) (°(C/W)						
70			Epoxy	printed r thickne	circuit b ss: 35 µ	oard FR4, m	- D'PAK	
60								
50								
40								
30								
20								
10						S _(Cu) (cm²)	
0 0	5	10	15	20	25	30	35 40	

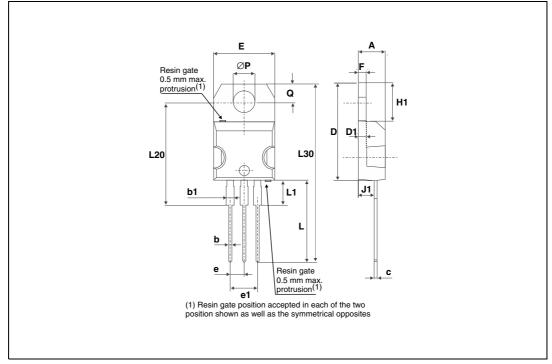
Figure 7. Thermal resistance junction to ambient versus copper surface under tab (typical values)

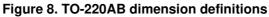


2 Package Information

- Epoxy meets UL94,V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.4 to 0.6 N·m (TO-220AB)

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK[®] is an ST trademark.







Dimensions							
Ref.	Millime	eters	Inches				
	Min.	Max.	Min.	Max.			
А	4.40	4.60	0.17	0.18			
b	0.61	0.88	0.024	0.035			
b1	1.14	1.70	0.045	0.067			
С	0.48	0.70	0.019	0.027			
D	15.25	15.75	0.60	0.62			
D1	1.27 t	yp.	0.05 typ.				
Е	10	10.40	0.39	0.41			
е	2.40	2.70	0.094	0.106			
e1	4.95	5.15	0.19	0.20			
F	1.23	1.32	0.048	0.052			
H1	6.20	6.60	0.24	0.26			
J1	2.40	2.72	0.094	0.107			
L	13	14	0.51	0.55			
L1	3.50	3.93	0.137	0.154			
L20	16.40	typ.	0.64	typ.			
L30	28.90	typ.	1.13	typ.			
ØP	3.75	3.85	0.147	0.151			
Q	2.65	2.95	0.104	0.116			

Table 5. TO-220AB dimension values



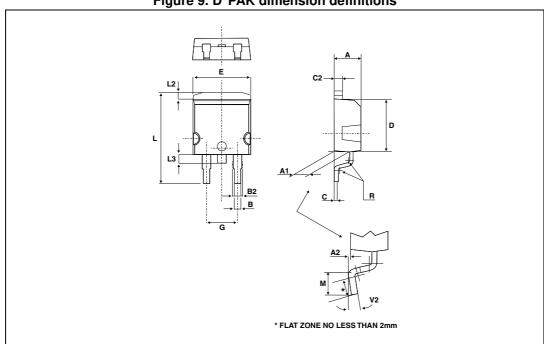


Figure 9. D²PAK dimension definitions

Table 6. D²PAK dimension values

	Dimensions						
Ref.	Millin	neters	Inches				
	Min.	Max.	Min.	Max.			
Α	4.40	4.60	0.173	0.181			
A1	2.49	2.69	0.098	0.106			
A2	0.03	0.23	0.001	0.009			
В	0.70	0.93	0.027	0.037			
B2	1.14	1.70	0.045	0.067			
С	0.45	0.60	0.017	0.024			
C2	1.23	1.36	0.048	0.054			
D	8.95	9.35	0.352	0.368			
E	10.00	10.40	0.393	0.409			
G	4.88	5.28	0.192	0.208			
L	15.00	15.85	0.590	0.624			
L2	1.27	1.40	0.050	0.055			
L3	1.30	1.75	0.051	0.069			
М	2.29	2.79	0.090	0.110			
R	0.40) typ.	0.016	6 typ.			
V2	0°	8°	0°	8°			



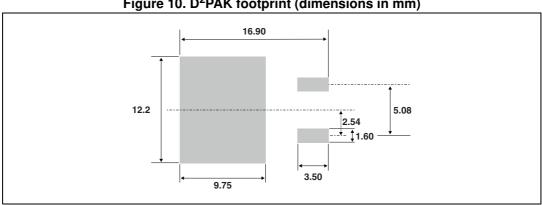


Figure 10. D²PAK footprint (dimensions in mm)



3 Ordering Information

Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
FERD40U45CT	FERD40U45CT	TO-220AB	2.2 g	50	Tube
FERD40U45CG-TR	FERD40U45CG	D ² PAK	1.8 g	500	Tape and reel

4 Revision history

Table 8. Document revision history

Date	Revision	Description of Changes
13-Nov-2013	1	Previous version



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